

TOSHIBA Field-Effect Transistor Silicon P-Channel MOS Type

# SSM3J317T

○ Power Management Switch Applications

○ High-Speed Switching Applications

- 1.8-V drive
- Low ON-resistance:  $R_{on} = 306 \text{ m}\Omega$  (max) (@ $V_{GS} = -1.8 \text{ V}$ )  
                           :  $R_{on} = 144 \text{ m}\Omega$  (max) (@ $V_{GS} = -2.8 \text{ V}$ )  
                           :  $R_{on} = 107 \text{ m}\Omega$  (max) (@ $V_{GS} = -4.5 \text{ V}$ )

## Absolute Maximum Ratings (Ta = 25°C)

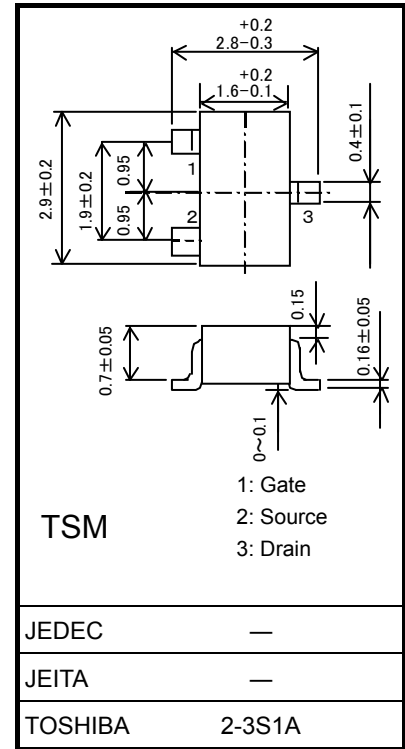
Characteristics		Symbol	Rating	Unit
Drain-Source voltage		$V_{DSS}$	-20	V
Gate-Source voltage		$V_{GSS}$	$\pm 8$	V
Drain current	DC	$I_D$ (Note 1)	-3.6	A
	Pulse	$I_{DP}$ (Note 1)	-7.2	
Drain power dissipation	$P_D$ (Note 2)		700	mW
	$t = 5\text{s}$		1400	
Channel temperature		$T_{ch}$	150	°C
Storage temperature range		$T_{stg}$	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.  
 Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: The junction temperature should not exceed 150°C during use.

Note 2: Mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Unit: mm



Weight: 10 mg (typ.)

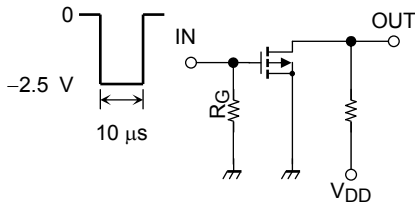
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-Source breakdown voltage		$V_{(BR)DSS}$	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	—	—	V
		$V_{(BR)DSX}$	$I_D = -1 \text{ mA}, V_{GS} = 8 \text{ V}$	-12	—	—	
Drain cut-off current		$I_{DSS}$	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	$\mu\text{A}$
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 1$	$\mu\text{A}$
Gate threshold voltage		$V_{th}$	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$	-0.3	—	-1.0	V
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -3 \text{ V}, I_D = -1.0 \text{ A}$ (Note 3)	2.2	4.4	—	S
Drain-source ON-resistance		$R_{DS(ON)}$	$I_D = -1.0 \text{ A}, V_{GS} = -4.5 \text{ V}$ (Note 3)	—	83	107	m $\Omega$
			$I_D = -0.75 \text{ A}, V_{GS} = -2.8 \text{ V}$ (Note 3)	—	107	144	
			$I_D = -0.5 \text{ A}, V_{GS} = -1.8 \text{ V}$ (Note 3)	—	170	306	
Input capacitance		$C_{iss}$		—	390	—	pF
Output capacitance		$C_{oss}$	$V_{DS} = -10 \text{ V}, V_{GS} = -0 \text{ V}, f = 1 \text{ MHz}$	—	67	—	
Reverse transfer capacitance		$C_{rss}$		—	55	—	
Total Gate Charge		$Q_g$	$V_{DS} = -10 \text{ V}, I_{DS} = -3.6 \text{ A}$ $V_{GS} = -4 \text{ V}$	—	9.6	—	nC
Gate-Source Charge		$Q_{gs}$		—	6.6	—	
Gate-Drain Charge		$Q_{gd}$		—	3.0	—	
Switching time	Turn-on time	$t_{on}$	$V_{DD} = -10 \text{ V}, I_D = -1.0 \text{ A}$	—	17	—	ns
	Turn-off time	$t_{off}$	$V_{GS} = 0 \text{ to } -2.5 \text{ V}, R_G = 4.7 \Omega$	—	19.5	—	
Drain-Source forward voltage		$V_{DSF}$	$I_D = 3.6 \text{ A}, V_{GS} = 0 \text{ V}$ (Note 3)	—	0.9	1.2	V

Note3: Pulse test

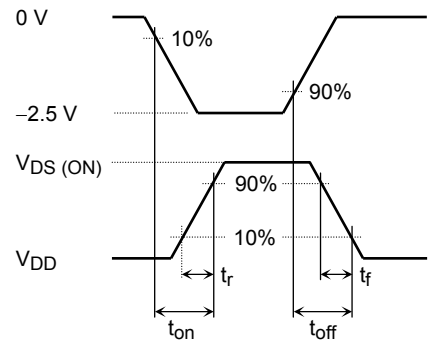
## Switching Time Test Circuit

(a) Test Circuit



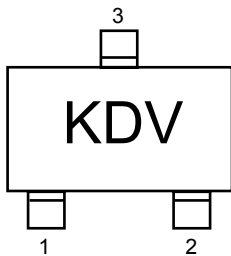
$V_{DD} = -10\text{ V}$   
 $R_G = 4.7\Omega$   
 D.U.  $\leq 1\%$   
 $V_{IN}$ :  $t_r, t_f < 5\text{ ns}$   
 Common Source  
 $T_a = 25^\circ\text{C}$

(b)  $V_{IN}$

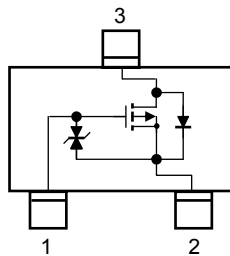


(c)  $V_{OUT}$

## Marking



## Equivalent Circuit (top view)



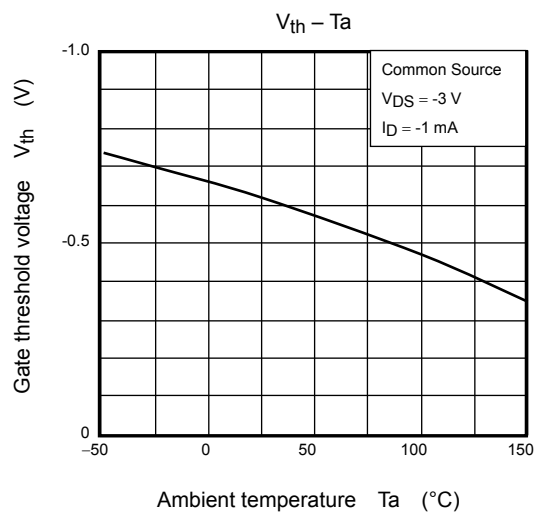
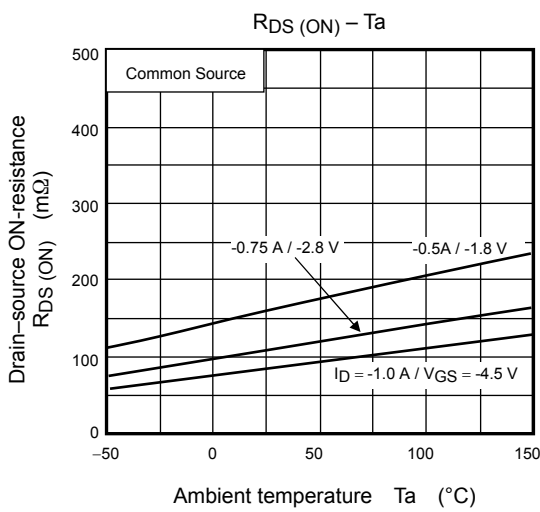
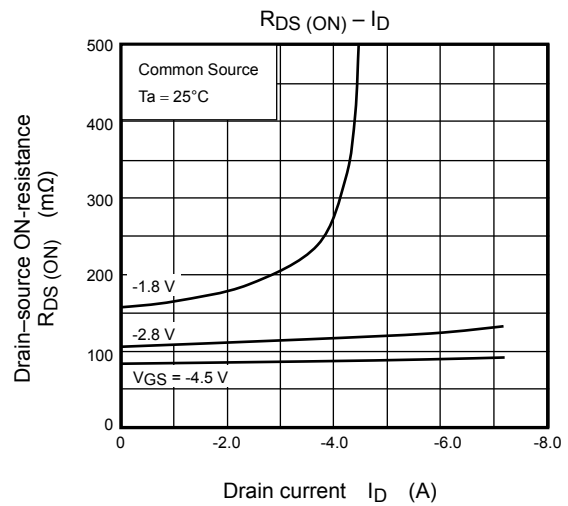
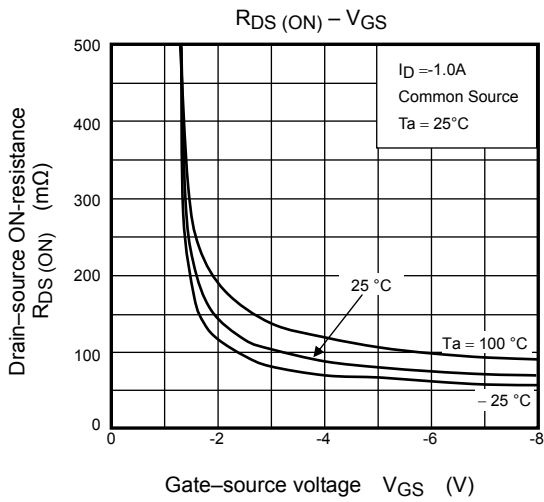
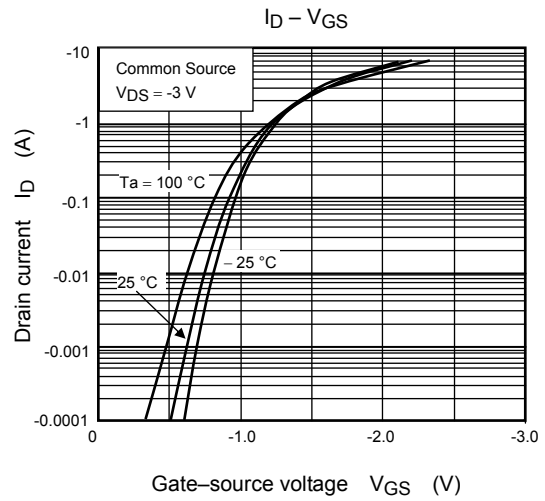
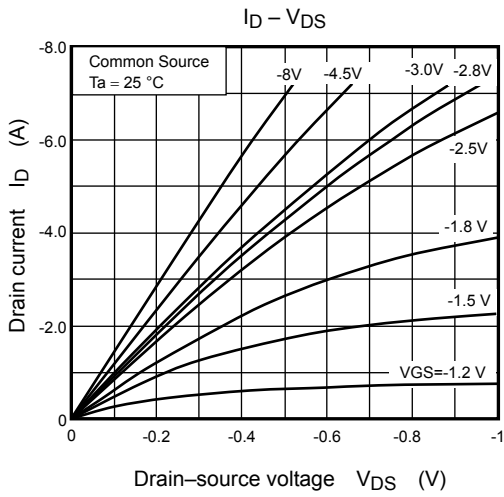
## Usage Considerations

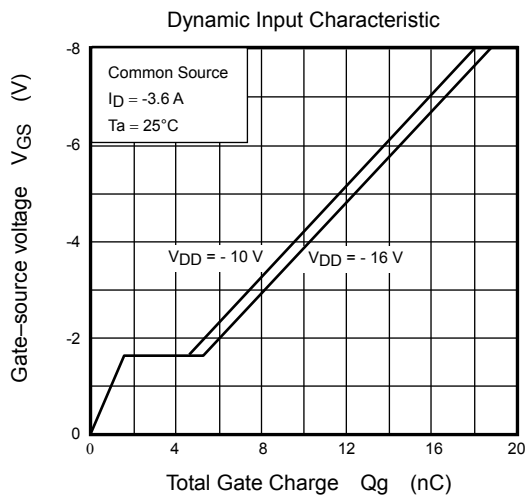
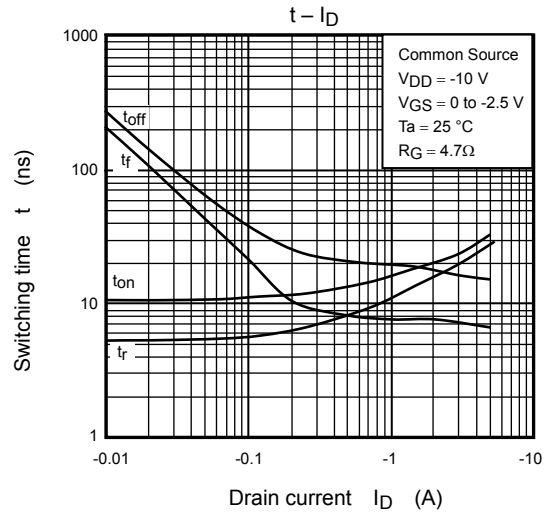
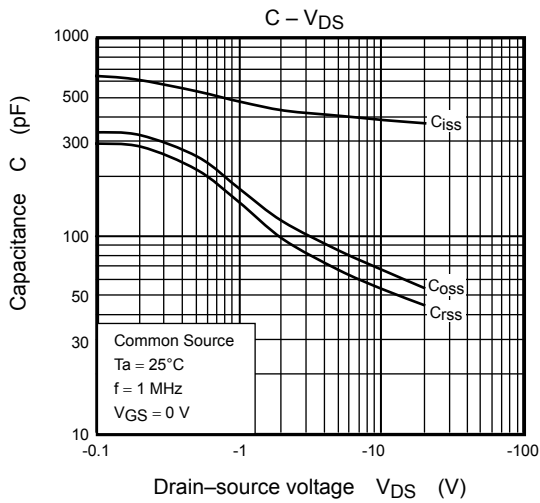
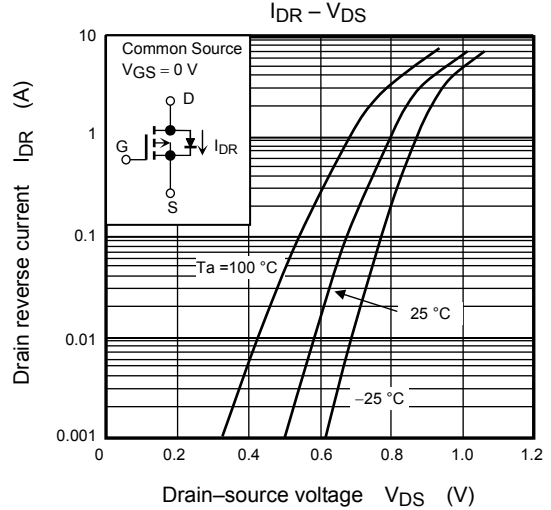
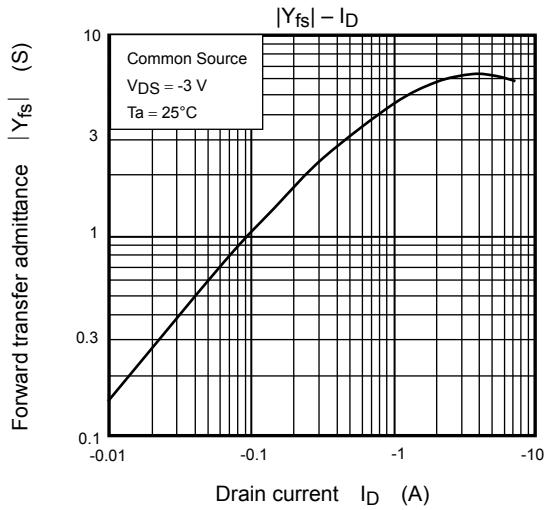
Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to be below ( $-1\text{ mA}$  for the Q2 of the SSM3J317T). Then, for normal switching operation,  $V_{GS(on)}$  must be higher than  $V_{th}$ , and  $V_{GS(off)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(off)} < V_{th} < V_{GS(on)}$ .

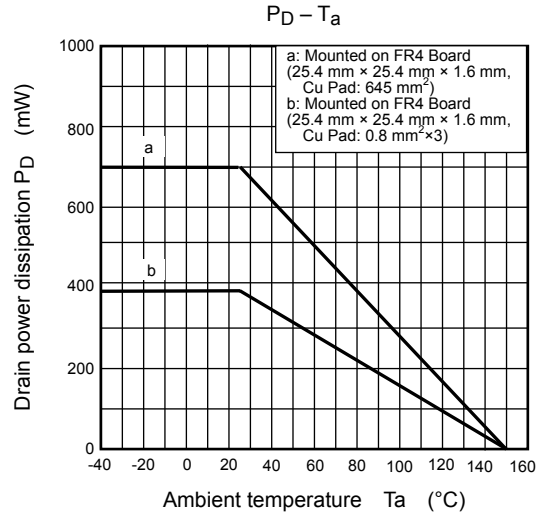
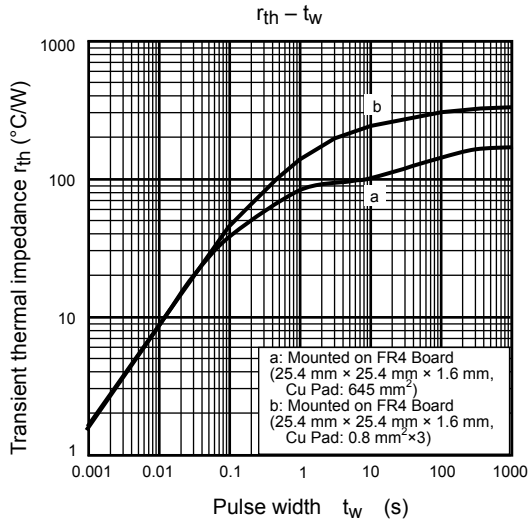
Take this into consideration when using the device.

## Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.







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